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Power Matters[™]

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Overview Diagrams

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Collector to Emitter Saturation Voltage

DC Current Gain	HFE		20.00		1	00.00	
Maximum Electrical Rating		Symbo	ol l	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)		V _{BR(CBO)}				50.00	V
Collector Current (dc)		I _C				6.00	А
Collector-Emitter Voltage (Base Open)		V_{CEO}				40.00	V
nitter-Base Voltage (Collector Open)		V _{EBO}				5.00	V
Power Dissipation, Total		Рт				40.00	W

This part can be found in the following product categories:

- Discretes ► Transistors ► BJT(BiPolar Junction Transistor) ► PNP Transistor
- Non-Radiation Hardened Devices ➤ Transistors ➤ BJT(BiPolar Junction Transistor) ➤ NPN Transistor

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